Nove pobude za delo v IEC – OKTOBER 2026

Referenčna oznaka	Naslov	Tehnični odbor	Odbor (SIST)
105/1180/NP	PNW TS 105-1180 ED1: Fuel cell modules - SOFC module interface specifications	TC 105	NI AKTIVNO PODROČJE
110/1902/NP	PNW 110-1902 ED1: 3D displays – Part 502-1: Measurement methods of plane-symmetrical real-image-forming optics for aerial display – Optical	TC 110	NI AKTIVNO PODROČJE
110/1904/NP	PNW 110-1904 ED1: 3D displays – Part 41-2: Measurement method of holographic display – Visible resolution and monochromatic speckle contrast	TC 110	NI AKTIVNO PODROČJE
113/1009/NP	PNW TS 113-1009 ED1: Nanomanufacturing - Key control characteristics - Part 3-7: Nanophotonic products - Spectral radiance of quantum dot enabled light-emitting diodes (QLED): Microscopic imaging	TC 113	NI AKTIVNO PODROČJE
21/1344/NP	PNW 21-1344 ED1: Gas analysis method of secondary lithium-ion cells for the propulsion of electric road vehicles	TC 21	NI AKTIVNO PODROČJE
37/548/NP	PNW 37-548 ED1: General Requirements for Non-linear Metal Oxide Resistors for Surge Arresters	TC 37	SIST/TC POD
38/871/NP	PNW 38-871 ED1: Instrument Transformers - Part 7: Additional requirements for Low Power Voltage Transformers (LPVT)	TC 38	NI AKTIVNO PODROČJE
38/872/NP	PNW 38-872 ED1: Instrument Transformers - Part 8: Additional requirements for Low Power Current Transformers (LPCT)	TC 38	NI AKTIVNO PODROČJE
47/3050/NP	PNW 47-3050 ED1: Semiconductor devices – Neuromorphic devices- Part 7: Evaluation method of synaptic decay time in memristor devices	TC 47	NI AKTIVNO PODROČJE
47D/1017/NP	PNW 47D-1017 ED1: Date Code of individual electronic components	SC 47D	NI AKTIVNO PODROČJE
47F/576/NP	PNW 47F-576 ED1: Semiconductor devices – Micro-electromechanical devices – Part 68: Test methods for magnetostriction coefficient of MEMS magnetic thin films	SC 47F	NI AKTIVNO PODROČJE
47F/577/NP	PNW 47F-577 ED1: Semiconductor devices - Micro-electromechanical devices - Part 69: MEMS packaging residual stress test methods based on stress amplification structure	SC 47F	NI AKTIVNO PODROČJE
47F/582/NP	PNW 47F-582 ED1: Semiconductor devices – Micro-electromechanical devices – Part 70 :Double Cantilever Beam Test with Compliance Measurement for MEMS Hybrid Bonding Interface Characterization	SC 47F	NI AKTIVNO PODROČJE
51/1641/NP	PNW 51-1641 ED1: Molded Inductors – Guidelines on the limits of surface irregularities	TC 51	NI AKTIVNO PODROČJE
65/1258/NP	PNW TS 65-1258 ED1: Security Requirements and their Application for AI Systems	TC 65	SIST/TC MOV

82/2706/NP	PNW 82-2706 ED1: Photovoltaic power generating systems connection with grid - Testing of power conversion equipment - Part 2: Testing environment	TC 82	SIST/TC PVS
88/1216/NP	PNW 88-1216 ED1: Offshore wind resource and energy yield assessment	TC 88	NI AKTIVNO PODROČJE
91/2149/NP	PNW 91-2149 ED1: Test methods for electrical materials, circuit board and other interconnection structures and assemblies - Part 5-507: General test methods for materials and assemblies - Controlled condensation testing	TC 91	NI AKTIVNO PODROČJE
JTC1-SC41/654/NP	PNW JTC1-SC41-654 ED1: Autonomous Digital Twins — Part 1: Architectural framework and foundational principles	ISO/IEC JTC 1/SC 41	NI AKTIVNO PODROČJE
86B/5306/NP	PNW 86B-5306 ED1: Fibre optic interconnecting devices and passive components – Connector optical interfaces for enhanced macrobend multimode fibres – Part 3-83: Connector parameters of physically contacting 50 µm core diameter fibres – Angled polyphenylene sulphide rectangular ferrules with a single row of 16 fibres for reference connector applications	SC 86B	SIST/TC MOC